

GP3D010A120S

VDC	1200 V
Q _c	53 nC
I _F	10 A
T _j ,max	175 °C

Amp+[™] Features

- Unipolar rectifier with surge current
- Zero reverse recovery current
- Fast, temperature-independent switching
- All parts tested to 1400V

Amp+[™] Benefits

- Near zero switching loss
- Higher efficiency
- Smaller heat sink
- Easy to parallel

Amp+[™] Applications

- Pulsed Power Generator/Converter
- Switch mode power supplies
- Anti-Parallel / Free-Wheeling Diode
- LED and HID Lighting

Package



Part #	Package	Marking
GP3D010A120S	SMC (DO-214AB)	S10A12



Maximum Ratings, at Ti=25 °C, unless otherwise specified

Characteristics	Symbol	Conditions	Values	Unit	
Continuous forward current	I _{F**}	T _L =25 °C, T _j =175 °C	6		
		T _L =125 °C, T _j =175 °C	3	A	
		T _L =150 °C, T _j =175 °C	2		
Surge non-repetitive forward current		T _L =25 °C, t _p =8.3 ms	112	۸	
sine halfwave	FSM	T _L =110 °C, t _p =8.3 ms	100	A	
Non-repetitive peak forward current	I _{F,max}	T _L =25 °C, t _p =10 μs	650	А	
<i>i²t</i> value	∫i²dt	T _L =25 °C, t _p =8.3 ms	52	A ² s	
		T _L =110 °C, t _p =8.3 ms	42		
Repetitive peak reverse voltage	V _{RRM}	T _j =25 °C	1200	V	
Diode <i>dv/dt</i> ruggedness	dv/dt	Turn-on slew rate, repetitive	200	V/ns	
Power dissipation	P _{tot**}	T _L =25 °C	10	W	
Operating junction & storage temperature	T _j , T _{storage}	Continuous	-55175	°C	
Soldering temperature	T _{solder}	Wave soldering leads	260	°C	
Mounting torque		M3 Screw	1	N-m	

Note: T_L - Lead Temperature

Characteristics Sy	Symbol	Conditions	Values			l Insit
	Symbol		min.	typ.	max.	Unit
DC blocking voltage	V _{DC}	T _j =25 °C	1200	-	-	V
Breakdown voltage	V _{BR}	I _R =1,000μΑ, Τ _j =25°C	1400	-	-	V
	V _F	I _F =20A, T _j =25 °C	-	1.50	1.65	V
Diode forward voltage		I _F =20A, T _j =125 °C	-	1.84	-	
		I _F =20A, T _j =175 °C	-	2.12	2.70	
Reverse current	I _R	V _R =1,200V, T _j =25 °C	-	1	20	μA
		V _R =1,400V, Tj=25 °C	-	3	-	
		V _R =1,200V, T _j =125 °C	-	5	-	
		V _R =1,200V, T _j =175 °C	-	20	300	
Total capacitive charge	Q _C	V _R =800V, T _j =25 °C	-	53	-	nC
Total capacitance	с	V _R =1V, f=1 MHz	-	589	-	pF
		V _R =400V, f=1 MHz	-	51	-	
		V _R =800V, f=1 MHz	-	37	-	

Electrical Characteristics, at T_j =25 °C, unless otherwise specified

Thermal Characteristics

Characteristics Sym	Symbol	ol Conditions	Values			Unit
	Symbol		min.	typ.	max.	Onit
Thermal resistance, junction-lead	R_{thJL}	minimum recommended	-	14.5	-	°C/W
Thermal resistance, junction-ambient	R _{thJA}	pad size	-	115	-	°C/W
Thermal resistance, junction-ambient	R_{thJA}	1" square pad, 2oz Cu	-	73	-	°C/W

Typical Performance



Fig. 1 Forward Characteristics (parameterized on T_i)



Fig. 2 Reverse Characteristics (parameterized on T_j)



Fig. 3 Reverse Characteristics (parameterized on Tj)



Fig. 5 Current Derating



Fig. 4 Power Derating



Fig. 6 Capacitance

1200V SiC Schottky Diode



Fig. 7 Capacitive Charge



Fig. 8 Typical Capacitance Stored Energy



Fig. 9 Thermal Response, Junction to Lead



Fig. 10 Thermal Response, Junction to Ambient

1200V SiC Schottky Diode

Package Dimensions SMC (DO-214AB)



Dimensions in inches and (millimeters)

Recommended Minimum Pad Dimensions



Dimensions in inches and (millimeters)

1200V SiC Schottky Diode

Amp+™

GP3D010A120S

Tape & Reel Specification

Item	Symbol	Dimensions (mm)
Carrier Width	А	6.3 (max)
Carrier Length	В	8.6 (max)
Carrier Depth	С	2.9 (max)
Sprocket Hole	d	1.50 ± 0.1
Reel Outside Diameter	D	330 ± 2.0
Feed Hole Diameter	D0	13.5 ± 1
Reel Inner Diameter	D1	50 (min)
Sprocket Hole Position	E	1.75 ± 0.1
Punch Hole Position	F	7.5 ± 0.05
Sprocket Hole Pitch	Р	8.0 ± 0.1
Sprocket Hole Pitch	P0	4.0 ± 0.1
Embossment Center	P1	2.0 ± 0.1
Overall Tape Thickness	Т	0.6 (max)
Tape Width	W	16.0 ± 0.3
Reel Width	W2	22.4 (max)
Reel Width	W1	18.4 (max)



Revision History

Date	Revision	Notes
5/7/2021	1.0	Initial release of datasheet

<u>Notes</u>

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS2), as implemented March, 2013. RoHS Declarations for this product can be obtained from the Product Documentation sections of www.SemiQ.com.

REACh Compliance

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